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RF Micro Devices(R) Unveils rGaN-HV(TM) Process Technology for Power Device Products and Foundry Customers

GREENSBORO, N.C., April 26, 2012 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced the extension of RFMD's industry-leading GaN process technology portfolio to include a new technology optimized for high voltage power devices in power conversion applications.

RFMD's newest GaN process technology -- rGaN-HV™ - enables substantial system cost and energy savings in power conversion applications ranging from 1 to 50 KW. RFMD's rGaN-HV delivers device breakdown voltages up to 900 volts, high peak current capability, and ultra-fast switching times for GaN power switches and diodes. The new technology complements RFMD's GaN 1 process, which is optimized for high power RF applications and delivers high breakdown voltage over 400 volts, and RFMD's GaN 2 process, which is optimized for high linearity applications and delivers high breakdown voltage over 300 volts. RFMD will manufacture discrete power device components for customers in its Greensboro, NC, wafer fabrication facility (fab) and provide access to rGaN-HV to foundry customers for their customized power device solutions.

Bob Bruggeworth, President and Chief Executive Officer of RFMD, said, "The global demand for energy savings through improved power conversion efficiency is creating a tremendous opportunity for high-performance power devices based on RFMD's GaN power process technologies. We expect our newest GaN power process will expand our opportunities in the high-voltage power semiconductor market, and we are pleased to provide access to rGaN-HV to our external foundry customers to support their success in the high-performance power device market."

RFMD's Power Conversion Devices Product Line and Foundry Services Business Unit will exhibit a broad portfolio of GaN technologies and GaN power products at the PCIM Power Industry Conference, May 8-10, in Nuremberg, Germany. More information on RFMD's foundry services can be obtained by contacting RFMDFoundryServices@rfmd.com or by clicking on <http://www.rfmd.com/products/powerconversion/>

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001-, ISO 14001-, and ISO/TS 16949-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy,

assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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